



Vishay Semiconductors

RoHS

COMPLIANT HALOGEN

FREE

# Ultralow V<sub>F</sub> Ultrafast Rectifier, 6 A FRED Pt<sup>®</sup>

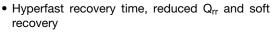




D-PAK	(TO:	-252A	(A)

PRODUCT SUMMARY						
Package	D-PAK (TO-252AA)					
I <sub>F(AV)</sub>	6 A					
$V_{R}$	600 V					
V <sub>F</sub> at I <sub>F</sub>	2.1 V					
t <sub>rr</sub> (typ.)	18 ns					
T <sub>J</sub> max.	175 °C					
Diode variation	Single die					

#### **FEATURES**





• For PFC CRM/CCM operation

· Low forward voltage drop

· Low leakage current

• Meets MSL level 1, per J-STD-020, LF maximum peak of 260 °C

• Compliant to RoHS Directive 2002/95/EC

• Halogen-free according to IEC 61249-2-21 definition

#### **DESCRIPTION/APPLICATIONS**

State of the art hyperfast recovery rectifiers designed with optimized performance of forward voltage drop, hyperfast recovery time, and soft recovery.

The planar structure and the platinum doped life time guarantee the best overall ruggedness and reliability characteristics.

These devices are intended for use in PFC boost stage in the AC/DC section of SMPS inverters or as freewheeling diodes. Their extremely optimized stored charge and low recovery current minimize the switching losses and reduce over dissipation in the switching element and snubbers.

ABSOLUTE MAXIMUM RATINGS								
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS				
Peak repetitive reverse voltage	$V_{RRM}$		600	V				
Average rectified forward current	I <sub>F(AV)</sub>	T <sub>C</sub> = 144 °C	6					
Non-repetitive peak surge current	I <sub>FSM</sub>	T <sub>J</sub> = 25 °C	70	Α				
Peak repetitive forward current	I <sub>FM</sub>	$T_C = 144  ^{\circ}\text{C},  f = 20  \text{kHz},  d = 50  \%$	12					
Operating junction and storage temperatures	T <sub>J</sub> , T <sub>Stg</sub>		- 65 to 175	°C				

<b>ELECTRICAL SPECIFICATIONS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Breakdown voltage, blocking voltage	V <sub>BR</sub> , V <sub>R</sub>	Ι <sub>R</sub> = 100 μΑ	600	-	-				
Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 6 A	-	1.60	2.1	V			
		I <sub>F</sub> = 6 A, T <sub>J</sub> = 150 °C	-	1.26	1.7				
Deverage legicage gurrent		V <sub>R</sub> = V <sub>R</sub> rated	-	-	50				
Reverse leakage current	I <sub>R</sub>	T <sub>J</sub> = 150 °C, V <sub>R</sub> = V <sub>R</sub> rated	-	-	250	μA			
Junction capacitance	C <sub>T</sub>	V <sub>R</sub> = 600 V	-	3.5	=	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8	-	nH			

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# VS-6EWH06FN-M3

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<b>DYNAMIC RECOVERY CHARACTERISTICS</b> (T <sub>J</sub> = 25 °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time		$I_F = 1 A, dI_F/dt = 10$	00 A/μs, V <sub>R</sub> = 30 V	-	18	25			
		$I_F = 1 \text{ A, } dI_F/dt = 50 \text{ A/}\mu\text{s, } V_R = 30 \text{ V}$		-	22	-			
	t <sub>rr</sub>	T <sub>J</sub> = 25 °C	$I_F = 6 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 390 \text{ V}$	-	27	-	ns		
		T <sub>J</sub> = 125 °C		-	37	-			
Dook room ourrent	I <sub>RRM</sub>	T <sub>J</sub> = 25 °C		-	4.1	-	Α		
Peak recovery current		T <sub>J</sub> = 125 °C		-	5.3	-	A		
Reverse recovery charge		T <sub>J</sub> = 25 °C		-	57	-	20		
	Q <sub>rr</sub>	T <sub>J</sub> = 125 °C		-	103	-	nC		

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Maximum junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 65	-	175	°C			
Thermal resistance, junction to case per leg	$R_{thJC}$		-	-	3	°C/W			
Approximate weight				0.3		g			
Approximate weight				0.01		OZ.			
Marking device		Case style D-PAK (TO-252AA)		6EWH	106FN				





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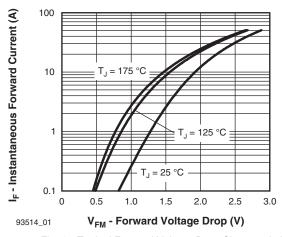


Fig. 1 - Typical Forward Voltage Drop Characteristics

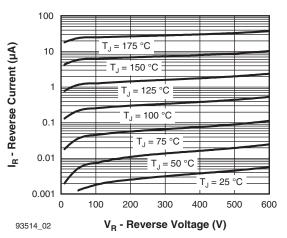


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

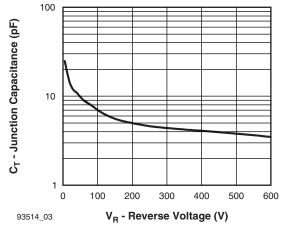


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

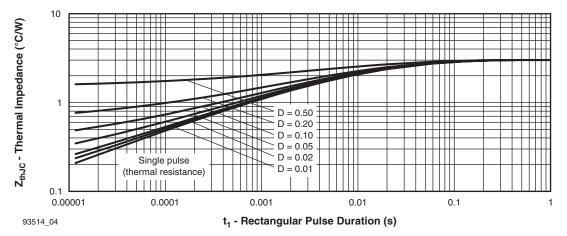


Fig. 4 - Maximum Thermal Impedance Z<sub>thJC</sub> Characteristics

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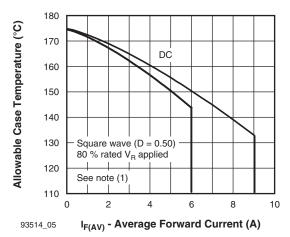


Fig. 5 - Maximum Allowable Case Temperature vs. Average Forward Current

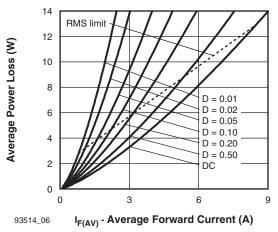


Fig. 6 - Forward Power Loss Characteristics

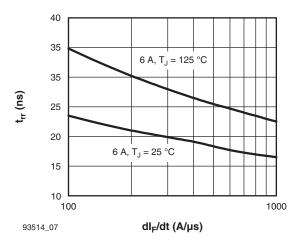


Fig. 7 - Typical Reverse Recovery Time vs. dI<sub>F</sub>/dt

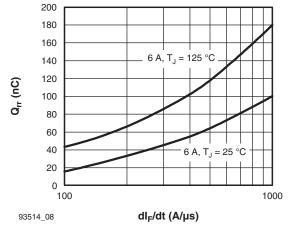


Fig. 8 - Typical Stored Charge vs. dl<sub>F</sub>/dt

#### Note

 $\begin{array}{ll} \mbox{(1)} & \mbox{Formula used: } T_C = T_J - (Pd + Pd_{REV}) \times R_{thJC}; \\ Pd = \mbox{Forward power loss} = I_{F(AV)} \times V_{FM} \mbox{ at } (I_{F(AV)}/D) \mbox{ (see fig. 6)}; \\ \end{array}$  $Pd_{REV}$  = Inverse power loss =  $V_{R1} \times I_R (1 - D)$ ;  $I_R$  at  $V_{R1}$  = Rated  $V_R$ 



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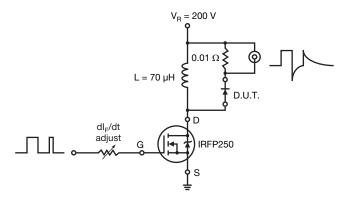
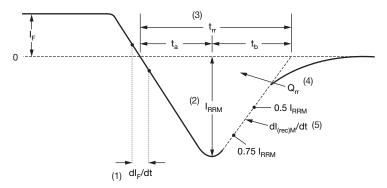


Fig. 9 - Reverse Recovery Parameter Test Circuit



- dl<sub>F</sub>/dt rate of change of current through zero crossing
- (2)  $I_{RRM}$  peak reverse recovery current
- (3)  $\rm t_{rr}$  reverse recovery time measured from zero crossing point of negative going  $\rm I_F$  to point where a line passing through 0.75  $\rm I_{RRM}$  and 0.50  $\rm I_{RRM}$  extrapolated to zero current.
- (4)  $Q_{rr}$  area under curve defined by  $t_{rr}$  and  $I_{BBM}$

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) dl<sub>(rec)M</sub>/dt - peak rate of change of current during t<sub>b</sub> portion of t<sub>rr</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

### VS-6EWH06FN-M3

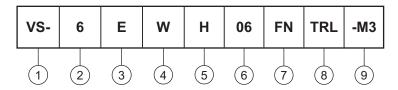
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#### **ORDERING INFORMATION TABLE**

Device code



Vishay Semiconductors product

Current rating (6 = 6 A)

Circuit configuration:

E = Single diode

4 Package identifier:

W = D-PAK

H = Hyperfast recovery

Voltage rating (06 = 600 V)

FN = TO-252AA

• None = Tube

• TR = Tape and reel

• TRL = Tape and reel (left oriented)

• TRR = Tape and reel (right oriented)

9 Environmental digit:

-M3 = Halogen-free, RoHS compliant and terminations lead (Pb)-free

ORDERING INFORMATION (Example)								
PREFERRED P/N	QUANTITY PER T/R	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION					
VS-6EWH06FN-M3	75	3000	Antistatic plastic tube					
VS-6EWH06FNTR-M3	2000	2000	13" diameter reel					
VS-6EWH06FNTRL-M3	3000	3000	13" diameter reel					
VS-6EWH06FNTRR-M3	3000	3000	13" diameter reel					

LINKS TO RELATED DOCUMENTS						
Dimensions	www.vishay.com/doc?95016					
Part marking information	www.vishay.com/doc?95176					
Packaging information	www.vishay.com/doc?95033					
SPICE model	www.vishay.com/doc?95187					



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**NOTES** 

3

2

MAX.

0.410

0.070

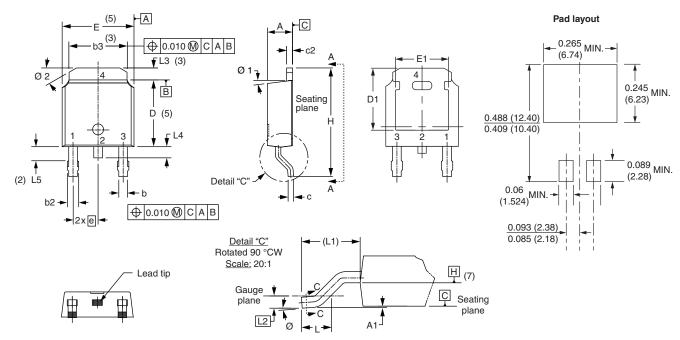
0.050

0.040

0.060

# **D-PAK (TO-252AA)**

#### **DIMENSIONS** in millimeters and inches



Ī	SYMBOL	MILLIMETERS		INCHES		NOTES	SYMBOL	MILLIMETERS		INCHES		
	STIVIDUL	MIN.	MAX.	MIN.	MAX.	NOTES		STIVIBUL	MIN.	MAX.	MIN.	MAX
ſ	Α	2.18	2.39	0.086	0.094			е	2.29	BSC	0.090	BSC
ſ	A1	-	0.13		0.005			Н	9.40	10.41	0.370	0.41
Ī	b	0.64	0.89	0.025	0.035			L	1.40	1.78	0.055	0.07
Ī	b2	0.76	1.14	0.030	0.045			L1	2.74	BSC	0.108	REF.
ſ	b3	4.95	5.46	0.195	0.215	3		L2	0.51 BSC		0.020 BSC	
Ī	С	0.46	0.61	0.018	0.024			L3	0.89	1.27	0.035	0.05
Ī	c2	0.46	0.89	0.018	0.035			L4	-	1.02	-	0.04
ſ	D	5.97	6.22	0.235	0.245	5		L5	1.14	1.52	0.045	0.06
Ī	D1	5.21	-	0.205	-	3		Ø	0°	10°	0°	10°
ſ	Е	6.35	6.73	0.250	0.265	5		Ø1	0°	15°	0°	15°
Ī	E1	4.32	-	0.170	-	3		Ø2	25°	35°	25°	35°

#### Notes

- (1) Dimensioning and tolerancing as per ASME Y14.5M-1994
- Lead dimension uncontrolled in L5
- Dimension D1, E1, L3 and b3 establish a minimum mounting surface for thermal pad
- Section C C dimension apply to the flat section of the lead between 0.13 and 0.25 mm (0.005 and 0.10") from the lead tip
- Dimension D, and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- Dimension b1 and c1 applied to base metal only
- (7) Datum A and B to be determined at datum plane H
- Outline conforms to JEDEC outline TO-252AA



### **Legal Disclaimer Notice**

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# **Material Category Policy**

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

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